Switch-mode Power Rectifiers

MBR830MFS, NRVB830MFS

SCHOTTKY BARRIER RECTIFIERS 8 AMPERES 30 VOLTS

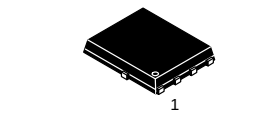
These state−of−the−art devices have the following features:

Features

- Low Power Loss / High Efficiency
- New Package Provides Capability of Inspection and Probe After Board Mounting
- Guardring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Wettable Flacks Option Available
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable*
- These are Pb−Free and Halide−Free Devices

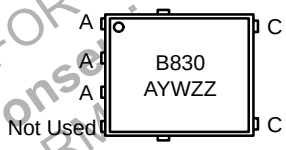
Mechanical Characteristics:

- Case: Epoxy, Molded
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements



SO−8 FLAT LEAD
CASE 488AA
STYLE 2

MARKING DIAGRAM



B830 = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	30	V
Average Rectified Forward Current (Rated V_R, T_C = 143°C)	$I_{F(AV)}$	8.0	A
Peak Repetitive Forward Current, (Rated V_R, Square Wave, 20 kHz, T_C = 143°C)	I_{FRM}	16	A
Non−Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	150	A
Storage Temperature Range	T_{stg}	−65 to +150	°C
Operating Junction Temperature	T_J	−40 to +150	°C
Unclamped Inductive Switching Energy (10 mH Inductor, Non−repetitive)	E_{AS}	100	mJ
ESD Rating (Human Body Model)		3B	
ESD Rating (Machine Model)		M4	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

NOTE: The heat generated must be less than the thermal conductivity from Junction−to−Ambient: dPD/dTJ < 1/RJA.

ORDERING INFORMATION

Device	Package	Shipping†
MBR830MFST1G	SO−8 FL (Pb−Free)	1500 / Tape & Reel
MBR830MFST3G	SO−8 FL (Pb−Free)	5000 / Tape & Reel
NRVB830MFST1G*	SO−8 FL (Pb−Free)	1500 / Tape & Reel
NRVB830MFST3G*	SO−8 FL (Pb−Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction−to−Case, Steady State (Assumes 600 mm^2 1 oz. copper bond pad, on a FR4 board)	$R_{\theta JC}$	−	2.0	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Instantaneous Forward Voltage (Note 1) (i_F = 8 Amps, T_J = 125°C) (i_F = 8 Amps, T_J = 25°C)	v_F	 0.44 0.50	 0.57 0.70	V
Instantaneous Reverse Current (Note 1) (Rated dc Voltage, T_J = 125°C) (Rated dc Voltage, T_J = 25°C)	i_R	 15 0.020	 50 0.200	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL CHARACTERISTICS

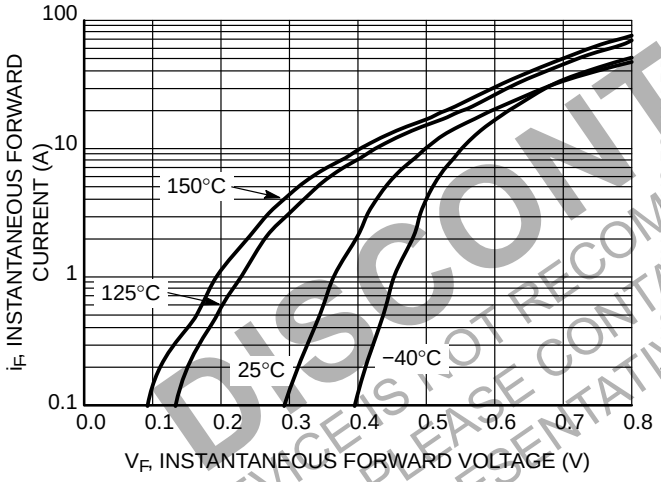


Figure 1. Typical Instantaneous Forward Characteristics

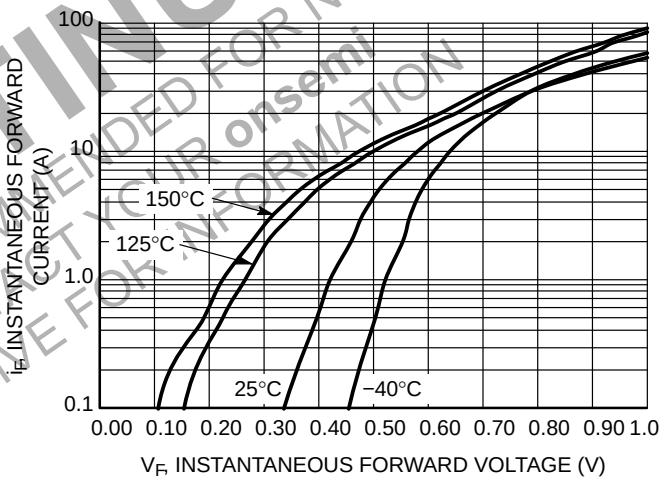


Figure 2. Maximum Instantaneous Forward Characteristics

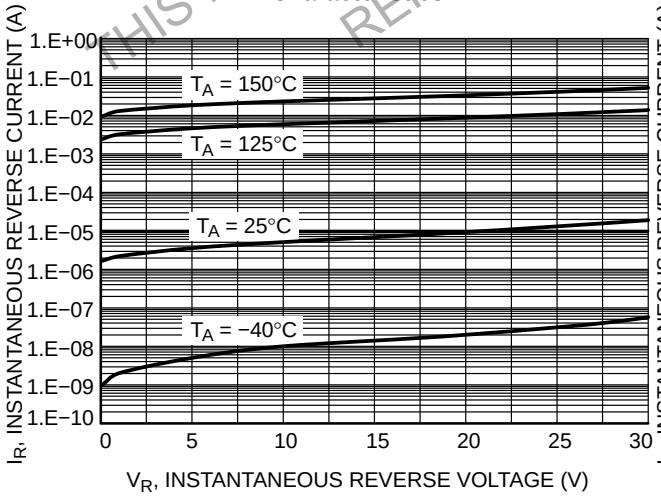


Figure 3. Typical Reverse Characteristics

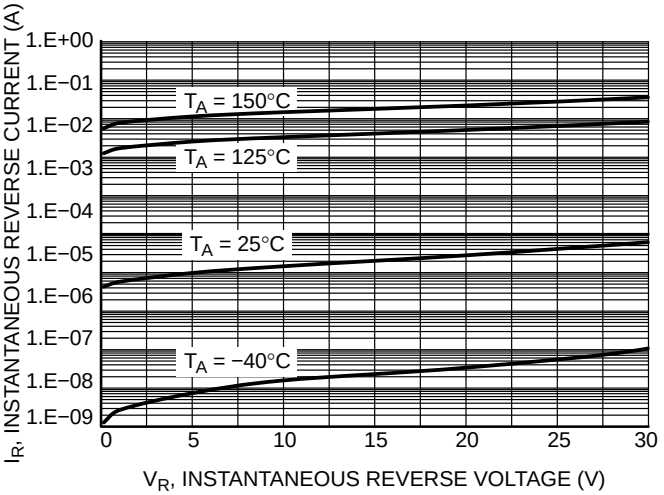


Figure 4. Maximum Reverse Characteristics

TYPICAL CHARACTERISTICS (Continued)

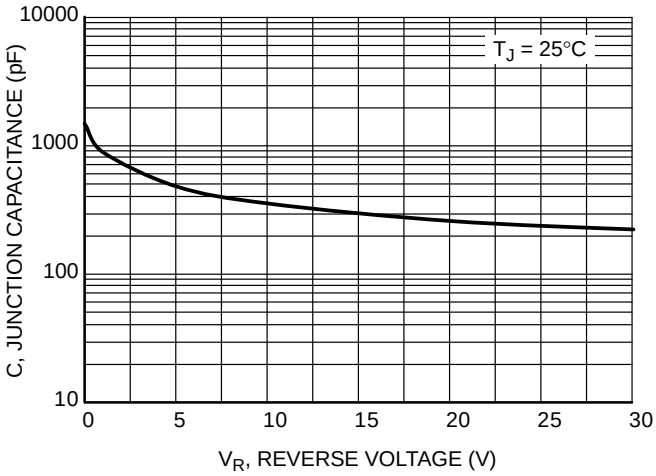


Figure 5. Typical Junction Capacitance

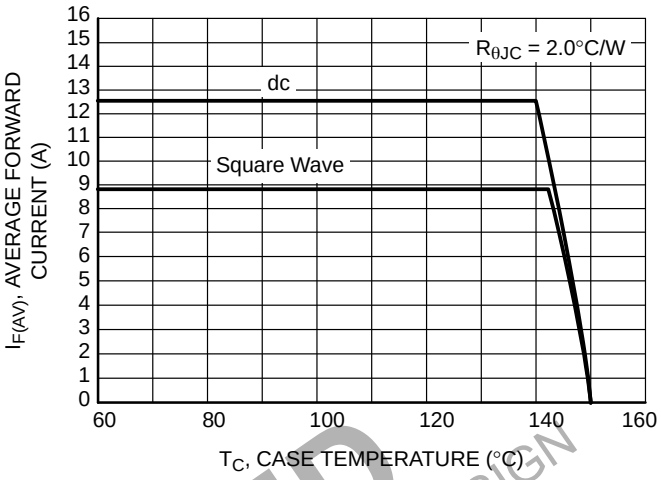


Figure 6. Current Derating TO−220AB

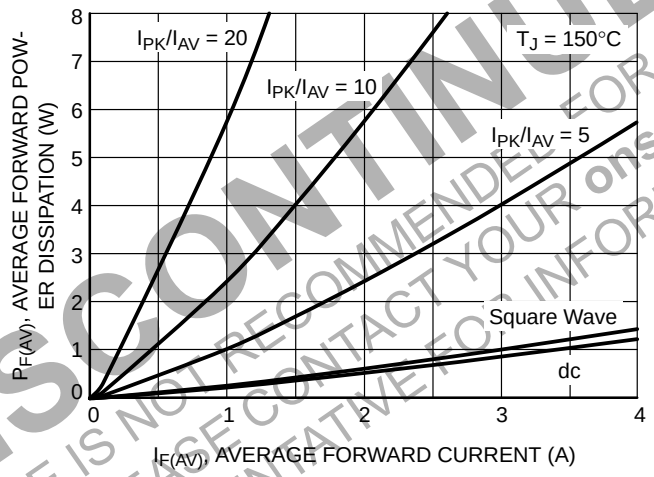


Figure 7. Forward Power Dissipation

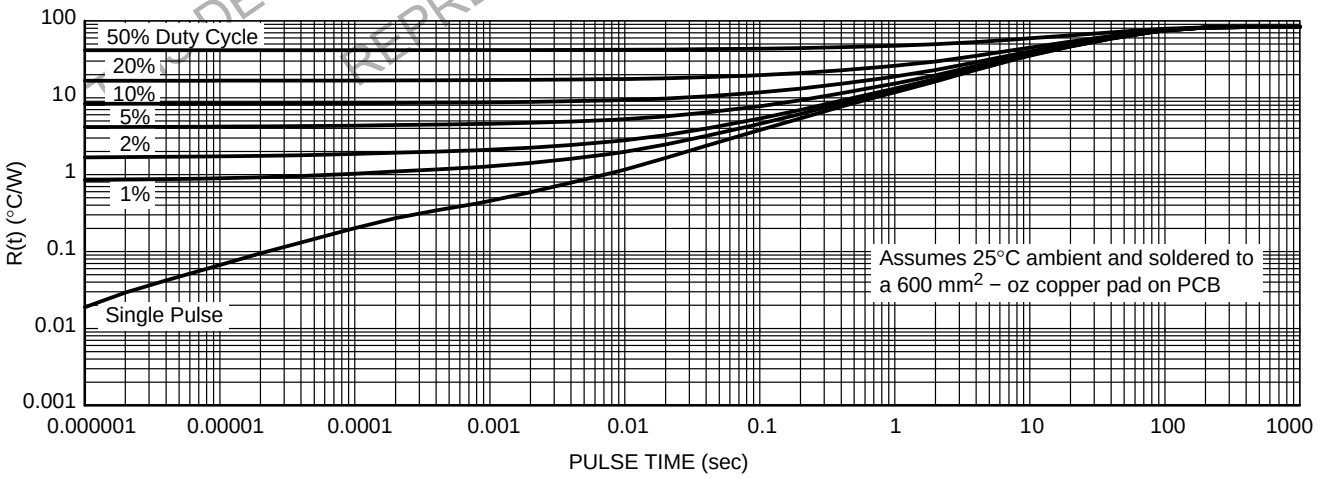
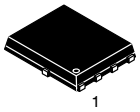


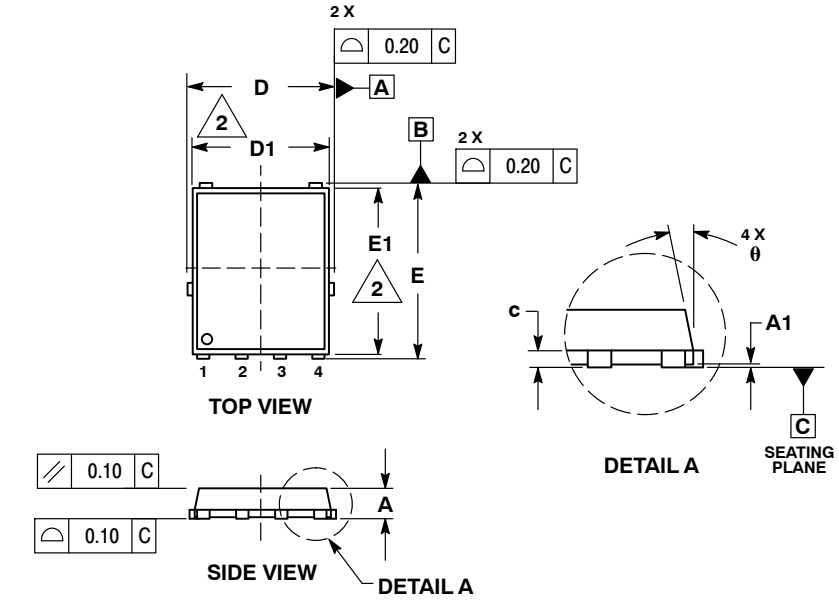
Figure 8. Thermal Response



SCALE 2:1

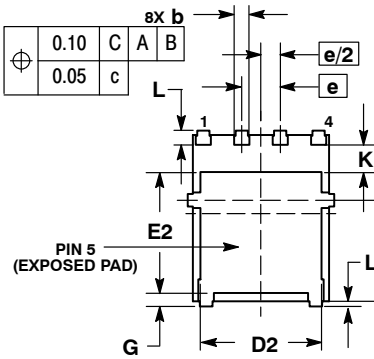
DFN5 5x6, 1.27P
(SO−8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

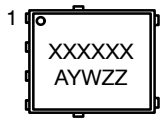


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	–––	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	–––	12 °



GENERIC MARKING DIAGRAM*



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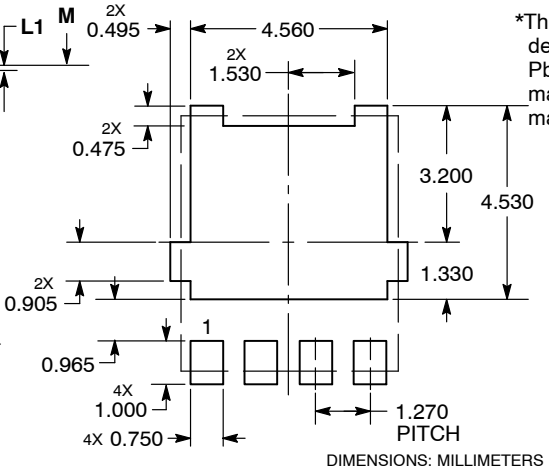
*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	**DFN5 5x6, 1.27P (SO−8FL)**		**PAGE 1 OF 1**

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